

General Purpose NPN Epitaxial Planar Transistor

BTN5551N3

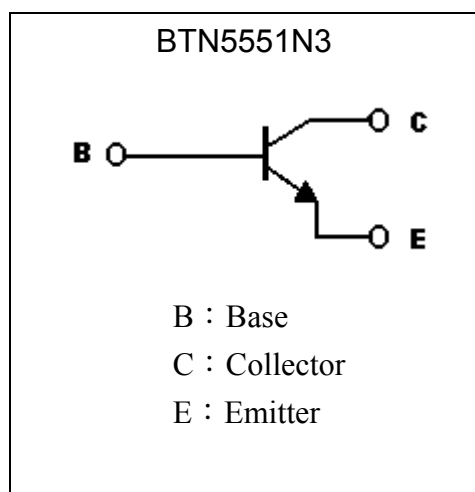
Description

The BTN5551N3 is designed for general purpose applications requiring high breakdown voltage.

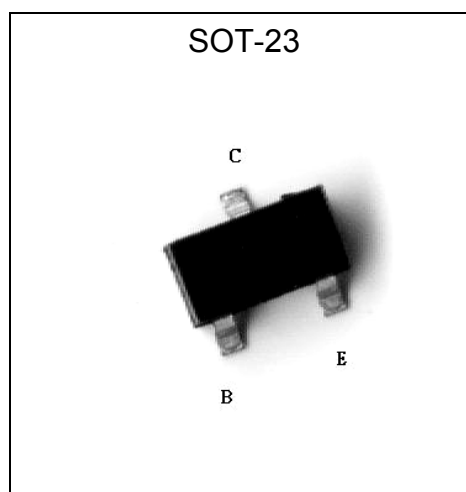
Features

- High collector-emitter breakdown voltage. ($BV_{CEO}=160V @ I_C=1mA$)
- Complement to BTP5401N3

Symbol



Outline



Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Limits | Unit |
|---------------------------|-----------|----------|------|
| Collector-Base Voltage | V_{CBO} | 180 | V |
| Collector-Emitter Voltage | V_{CEO} | 160 | V |
| Emitter-Base Voltage | V_{EBO} | 6 | V |
| Collector Current | I_C | 600 | mA |
| Power Dissipation | P_d | 225 | mW |
| Junction Temperature | T_j | 150 | °C |
| Storage Temperature | T_{stg} | -55~+150 | °C |

Characteristics (Ta=25°C)

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|------------------|------|------|------|------|----------------------------------|
| BV_{CBO} | 180 | - | - | V | $I_C=100\mu A$ |
| BV_{CEO} | 160 | - | - | V | $I_C=1mA$ |
| BV_{EBO} | 6 | - | - | V | $I_E=10\mu A$ |
| I_{CBO} | - | - | 50 | nA | $V_{CB}=120V$ |
| I_{EBO} | - | - | 50 | nA | $V_{EB}=4V$ |
| * $V_{CE(sat)1}$ | - | 0.1 | 0.15 | V | $I_C=10mA, I_B=1mA$ |
| * $V_{CE(sat)2}$ | - | - | 0.2 | V | $I_C=50mA, I_B=5mA$ |
| * $V_{BE(sat)1}$ | - | - | 1 | V | $I_C=10mA, I_B=1mA$ |
| * $V_{BE(sat)2}$ | - | - | 1 | V | $I_C=50mA, I_B=5mA$ |
| * h_{FE1} | 80 | - | - | - | $V_{CE}=5V, I_C=1mA$ |
| * h_{FE2} | 80 | - | - | - | $V_{CE}=5V, I_C=10mA$ |
| * h_{FE3} | 30 | - | - | - | $V_{CE}=5V, I_C=50mA$ |
| * h_{FE4} | 52 | - | 390 | - | $V_{CE}=6V, I_C=2mA$ |
| f_T | 100 | - | - | MHz | $V_{CE}=20V, I_C=10mA, f=100MHz$ |
| C_{ob} | - | - | 6 | pF | $V_{CB}=20V, I_E=0A, f=1MHz$ |

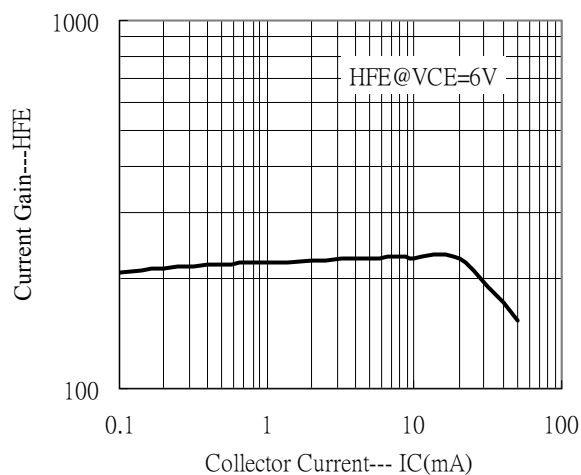
*Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of h_{FE4}

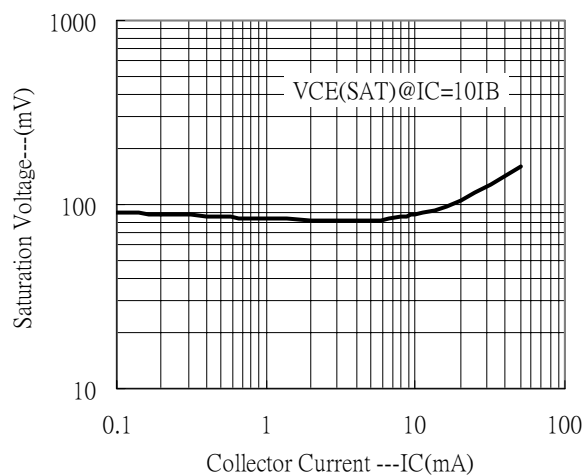
| Rank | K | P | Q | R |
|-------|--------|--------|---------|---------|
| Range | 52~120 | 82~180 | 120~270 | 180~390 |

Characteristic Curves

Current Gain vs Collector Current

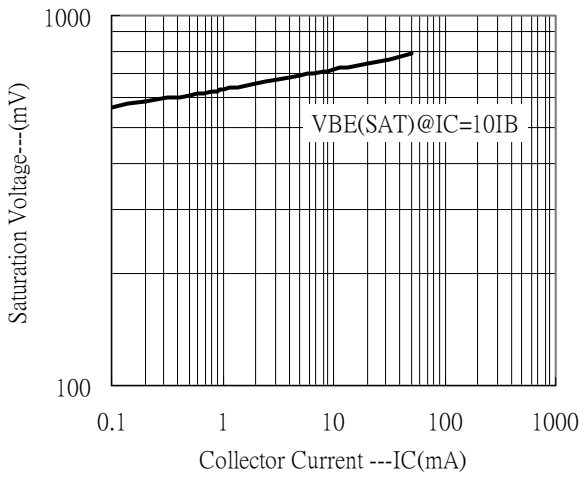


Saturation Voltage vs Collector Current

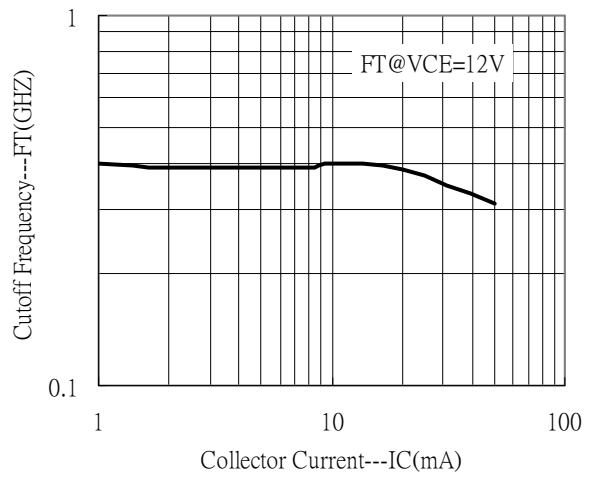




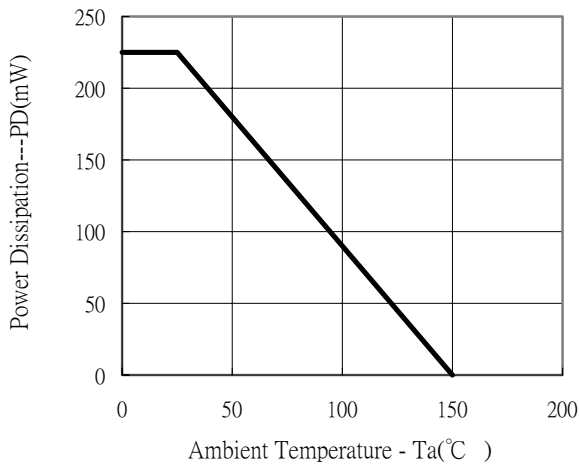
Saturation Voltage vs Collector Current



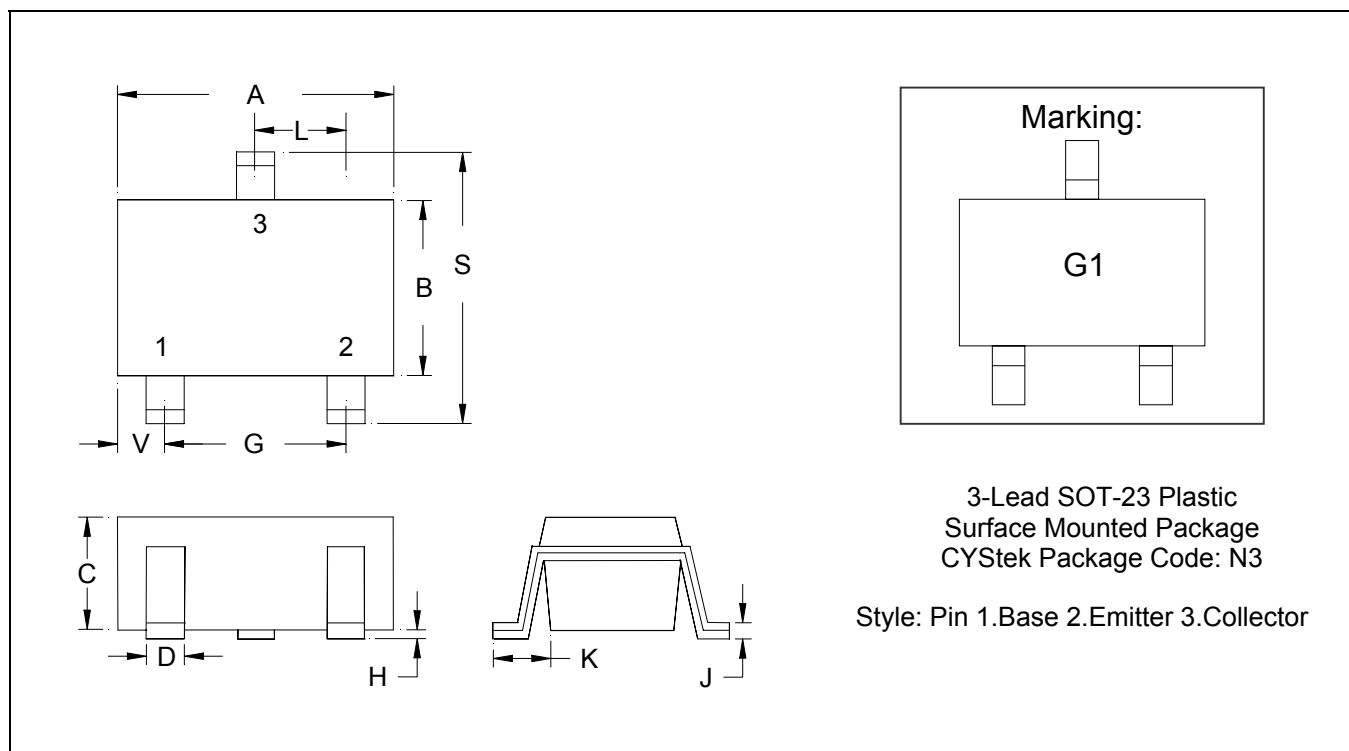
Cutoff Frequency vs Collector Current



Power Derating Curve



SOT-23 Dimension



*: Typical

| DIM | Inches | | Millimeters | | DIM | Inches | | Millimeters | |
|-----|--------|--------|-------------|------|-----|--------|--------|-------------|-------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| A | 0.1102 | 0.1204 | 2.80 | 3.04 | J | 0.0034 | 0.0070 | 0.085 | 0.177 |
| B | 0.0472 | 0.0630 | 1.20 | 1.60 | K | 0.0128 | 0.0266 | 0.32 | 0.67 |
| C | 0.0335 | 0.0512 | 0.89 | 1.30 | L | 0.0335 | 0.0453 | 0.85 | 1.15 |
| D | 0.0118 | 0.0197 | 0.30 | 0.50 | S | 0.0830 | 0.1083 | 2.10 | 2.75 |
| G | 0.0669 | 0.0910 | 1.70 | 2.30 | V | 0.0098 | 0.0256 | 0.25 | 0.65 |
| H | 0.0005 | 0.0040 | 0.013 | 0.10 | | | | | |

- Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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